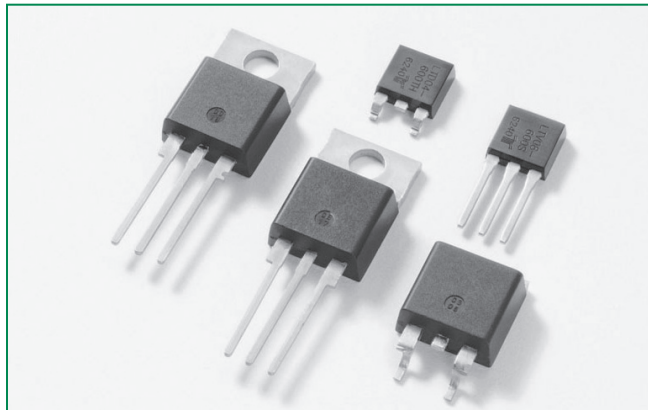


**RoHS Lxx06xx & Qxx06xx & Qxx06xHx Series**



**Description**

6 Amp bi-directional solid state switch series is designed for AC switching and phase control applications such as motor speed and temperature modulation controls, lighting controls, and static switching relays.

**Sensitive** type devices guarantee gate control in Quadrants I & IV needed for digital control circuitry.

**Standard** type devices normally operate in Quadrants I & III triggered from AC line.

**Alternistor** type devices only operate in quadrants I, II, & III and are used in circuits requiring high dv/dt capability.

**Features & Benefits**

- RoHS compliant
- Glass – passivated junctions
- Voltage capability up to 1000 V
- Surge capability up to 85 A
- Electrically isolated “L - Package” is UL recognized for 2500Vrms
- Solid-state switching eliminates arcing or contact bounce that create voltage transients
- No contacts to wear out from reaction of switching events
- Restricted (or limited) RFI generation, depending on activation point of sine wave
- Requires only a small gate activation pulse in each half-cycle

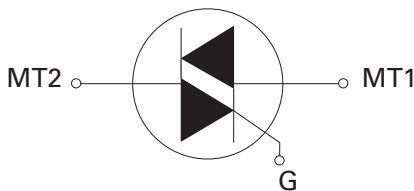
**Agency Approval**

Agency	Agency File Number
	L Package: E71639

**Main Features**

Symbol	Value	Unit
$I_{T(RMS)}$	6	A
$V_{DRM}/V_{RRM}$	400 to 1000	V
$I_{GT(Q1)}$	5 to 50	mA

**Schematic Symbol**



**Applications**

Excellent for AC switching and phase control applications such as heating, lighting, and motor speed controls.

Typical applications are AC solid-state switches, light dimmers, power tools, home/brown goods and white goods appliances.

Alternistor Triacs (no snubber required) are used in applications with extremely inductive loads requiring highest commutation performance.

Internally constructed isolated packages are offered for ease of heat sinking with highest isolation voltage.

**Absolute Maximum Ratings – Sensitive Triac (4 Quadrants)**

Symbol	Parameter	Value	Unit	
$I_{T(RMS)}$	RMS on-state current (full sine wave)	Lxx06Ly $T_C = 80^\circ C$	6	A
		Lxx06Vy / Lxx06Dy/ Lxx06Ry $T_C = 85^\circ C$		
$I_{TSM}$	Non repetitive surge peak on-state current (full cycle, $T_J$ initial = $25^\circ C$ )	f = 50 Hz $t = 20$ ms	50	A
		f = 60 Hz $t = 16.7$ ms		
$I^2t$	$I^2t$ Value for fusing	$t_p = 8.3$ ms	15	A <sup>2</sup> s
di/dt	Critical rate of rise of on-state current $I_G = 50$ mA with 0.1µs rise time	f = 120 Hz $T_J = 110^\circ C$	70	A/µs
$I_{GTM}$	Peak gate trigger current	$t_p \leq 10$ µs $T_J = 110^\circ C$	1.6	A
$P_{G(AV)}$	Average gate power dissipation	$T_J = 110^\circ C$	0.4	W
$T_{stg}$	Storage temperature range		-40 to 150	°C
$T_J$	Operating junction temperature range		-40 to 110	°C

Note: xx = voltage, y = sensitivity

**Absolute Maximum Ratings — Standard Triac**

Symbol	Parameter			Value	Unit	
$I_{T(RMS)}$	RMS on-state current (full sine wave)	Qxx06Ry / Qxx06Ny	$T_C = 95^\circ\text{C}$	6	A	
		Qxx06Ly	$T_C = 90^\circ\text{C}$			
$I_{TSM}$	Non repetitive surge peak on-state current (full cycle, $T_J$ initial = $25^\circ\text{C}$ )	f = 50 Hz	t = 20 ms	65	A	
		f = 60 Hz	t = 16.7 ms	80		
$I^2t$	$I^2t$ Value for fusing	$t_p = 8.3$ ms		26.5	$\text{A}^2\text{s}$	
di/dt	Critical rate of rise of on-state current $I_G = 200\text{mA}$ with $0.1\mu\text{s}$ rise time	f = 120 Hz	$T_J = 125^\circ\text{C}$	70	$\text{A}/\mu\text{s}$	
$I_{GTM}$	Peak gate trigger current	$t_p \leq 10 \mu\text{s}; I_{GT} \leq I_{GTM}$	$T_J = 125^\circ\text{C}$	1.6	A	
$P_{G(AV)}$	Average gate power dissipation	$T_J = 125^\circ\text{C}$		0.5	W	
$T_{stg}$	Storage temperature range				-40 to 150	$^\circ\text{C}$
$T_J$	Operating junction temperature range				-40 to 125	$^\circ\text{C}$

Note: xx = voltage, y = sensitivity

**Absolute Maximum Ratings — Alternistor Triac (3 Quadrants)**

Symbol	Parameter			Value	Unit	
$I_{T(RMS)}$	RMS on-state current (full sine wave)	Qxx06LHy		$T_C = 95^\circ\text{C}$	6	A
		Qxx06RH <sub>y</sub> / Qxx06NH <sub>y</sub> Qxx06VH <sub>y</sub> / Qxx06DH <sub>y</sub>		$T_C = 100^\circ\text{C}$		
$I_{TSM}$	Non repetitive surge peak on-state current (full cycle, $T_J$ initial = $25^\circ\text{C}$ )	f = 50 Hz	t = 20 ms	Qxx06VHy Qxx06DHy	55	A
				Qxx06LHy Qxx06RH <sub>y</sub> Qxx06NH <sub>y</sub>	80	
		f = 60 Hz	t = 16.7 ms	Qxx06VHy Qxx06DHy	65	
				Qxx06LHy Qxx06RH <sub>y</sub> Qxx06NH <sub>y</sub>	85	
$I^2t$	$I^2t$ Value for fusing	$t_p = 8.3$ ms		Qxx06VHy Qxx06DHy	17.5	$\text{A}^2\text{s}$
				Qxx06LHy Qxx06RH <sub>y</sub> Qxx06NH <sub>y</sub>	30	
di/dt	Critical rate of rise of on-state current	f = 120 Hz		$T_J = 125^\circ\text{C}$	70	$\text{A}/\mu\text{s}$
$I_{GTM}$	Peak gate trigger current	$t_p \leq 10 \mu\text{s}; I_{GT} \leq I_{GTM}$		$T_J = 125^\circ\text{C}$	1.6	A
$P_{G(AV)}$	Average gate power dissipation	$T_J = 125^\circ\text{C}$		0.5	W	
$T_{stg}$	Storage temperature range				-40 to 150	$^\circ\text{C}$
$T_J$	Operating junction temperature range				-40 to 125	$^\circ\text{C}$

Note: xx = voltage, y = sensitivity

**Electrical Characteristics (T<sub>J</sub> = 25°C, unless otherwise specified) — Sensitive Triac (4 Quadrants)**

Symbol	Test Conditions	Quadrant		Value			Unit
				Lxx06x5	Lxx06x6	Lxx06x8	
I <sub>GT</sub>	V <sub>D</sub> = 12V R <sub>L</sub> = 60 Ω	I – II – III IV	MAX.	5 5	5 10	10 20	mA
V <sub>GT</sub>		ALL	MAX.	1.3			V
V <sub>GD</sub>	V <sub>D</sub> = V <sub>DRM</sub> R <sub>L</sub> = 3.3 kΩ T <sub>J</sub> = 110°C	ALL	MIN.	0.2			V
I <sub>H</sub>	I <sub>T</sub> = 100mA		MAX.	10	10	20	mA
dv/dt	V <sub>D</sub> = V <sub>DRM</sub> Gate Open T <sub>J</sub> = 100°C	400V	TYP.	30	30	40	V/μs
(dv/dt)c		600V		20	20	30	
(di/dt)c	(di/dt)c = 3.2 A/ms T <sub>J</sub> = 110°C		TYP.	1	2	2	V/μs
t <sub>gt</sub>	I <sub>G</sub> = 2 × I <sub>GT</sub> PW = 15μs I <sub>T</sub> = 8.5 A(pk)		TYP.	3.0	3.0	3.2	μs

**Electrical Characteristics (T<sub>J</sub> = 25°C, unless otherwise specified) — Standard Triac**

Symbol	Test Conditions	Quadrant		Value		Unit
				Qxx06x4	Qxx06x5	
I <sub>GT</sub>	V <sub>D</sub> = 12V R <sub>L</sub> = 60 Ω	I – II – III IV	MAX. TYP.	25 50	50 75	mA
V <sub>GT</sub>		I – II – III	MAX.	1.3		V
V <sub>GD</sub>	V <sub>D</sub> = V <sub>DRM</sub> R <sub>L</sub> = 3.3 kΩ T <sub>J</sub> = 125°C	ALL	MIN.	0.2		V
I <sub>H</sub>	I <sub>T</sub> = 200mA		MAX.	50	50	mA
dv/dt	V <sub>D</sub> = V <sub>DRM</sub> Gate Open T <sub>J</sub> = 125°C	400V	MIN.	120		V/μs
		600V			100	
		800V			85	
	V <sub>D</sub> = V <sub>DRM</sub> Gate Open T <sub>J</sub> = 100°C	1000V			100	
(dv/dt)c	(di/dt)c = 3.2 A/ms T <sub>J</sub> = 125°C		TYP.	4	4	V/μs
t <sub>gt</sub>	I <sub>G</sub> = 2 × I <sub>GT</sub> PW = 15μs I <sub>T</sub> = 8.5 A(pk)		TYP.	3.0	3.0	μs

**Electrical Characteristics (T<sub>J</sub> = 25°C, unless otherwise specified) — Alternistor Triac (3 Quadrants)**

Symbol	Test Conditions	Quadrant		Value		Unit	
				Qxx06xH3	Qxx06xH4		
I <sub>GT</sub>	V <sub>D</sub> = 12V R <sub>L</sub> = 60 Ω	I – II – III	MAX.	10	35	mA	
V <sub>GT</sub>		I – II – III	MAX.	1.3		V	
V <sub>GD</sub>	V <sub>D</sub> = V <sub>DRM</sub> R <sub>L</sub> = 3.3 kΩ T <sub>J</sub> = 125°C	I – II – III	MIN.	0.2		V	
I <sub>H</sub>	I <sub>T</sub> = 100mA		MAX.	15	35	mA	
dv/dt	V <sub>D</sub> = V <sub>DRM</sub> Gate Open T <sub>J</sub> = 125°C	Qxx06VHy / Qxx06DHy	MIN.	400V	75	400	V/μs
				600V	50	300	
				800V		200	
		Qxx06LHy / Qxx06RHy / Qxx06NHx		400V	75	450	
				600V	50	350	
				800V		250	
	V <sub>D</sub> = V <sub>DRM</sub> Gate Open T <sub>J</sub> = 100°C	ALL			1000V		
(dv/dt)c	(di/dt)c = 3.2 A/ms T <sub>J</sub> = 125°C		MIN.	20	25	V/μs	
t <sub>gt</sub>	I <sub>G</sub> = 2 × I <sub>GT</sub> PW = 15μs I <sub>T</sub> = 8.5 A(pk)		TYP.	4.0	4.0	μs	

Note: xx = voltage, x = package, y = sensitivity

**Static Characteristics**

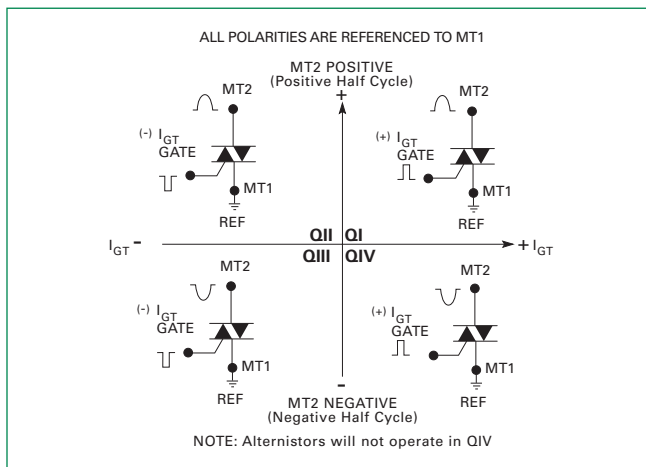
Symbol	Test Conditions			Value	Unit		
$V_{TM}$	$I_{TM} = 11.3A$ $t_p = 380 \mu s$			MAX.	1.60 V		
$I_{DRM} / I_{RRM}$	$V_{DRM} = V_{RRM}$	Lxx06xy	$T_J = 25^\circ C$	400 - 600V	MAX.	20 $\mu A$	
			$T_J = 110^\circ C$	400 - 600V		0.5 mA	
		Qxx06xy	$T_J = 25^\circ C$	400 - 1000V		50 $\mu A$	
			$T_J = 125^\circ C$	400 - 800V		2 mA	
			$T_J = 100^\circ C$	1000V			
		Qxx06xHy	$T_J = 25^\circ C$	400 - 800V		MAX.	10 $\mu A$
				1000V			20 $\mu A$
			$T_J = 125^\circ C$	400 - 800V			3 mA
			$T_J = 100^\circ C$	1000V			

**Thermal Resistances**

Symbol	Parameter	Value	Unit
$R_{\theta(J-C)}$	Junction to case (AC)	L/Qxx06Ryy / L/Qxx06Nyy	1.8
		L/Qxx06Lyy	3.3
		L/Qxx06Vyy / L/Qxx06Dyy	3.2
$R_{\theta(J-A)}$	Junction to ambient	L/Qxx06Ryy	45
		L/Qxx06Lyy	50
		L/Qxx06Vyy	70

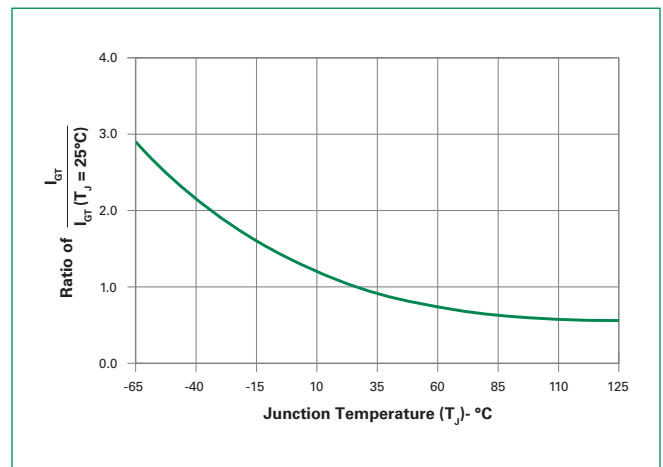
Note: xx = voltage, x = package, y = sensitivity, yy = type & sensitivity

**Figure 1: Definition of Quadrants**

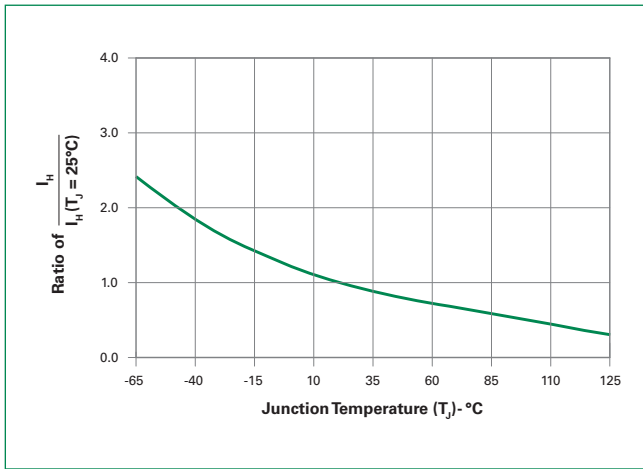


Note: Alternistors will not operate in QIV

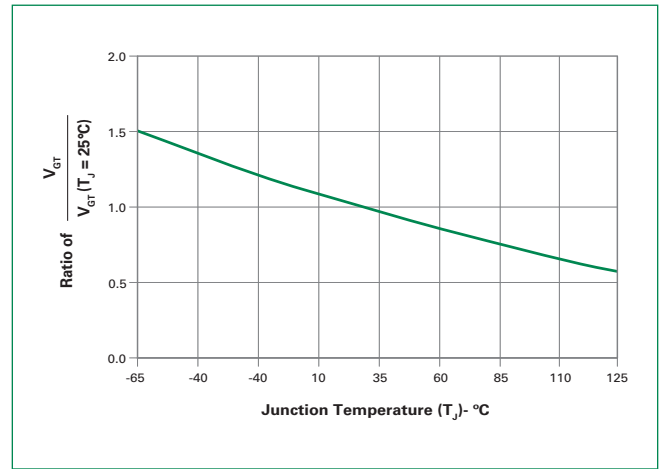
**Figure 2: Normalized DC Gate Trigger Current for All Quadrants vs. Junction Temperature**



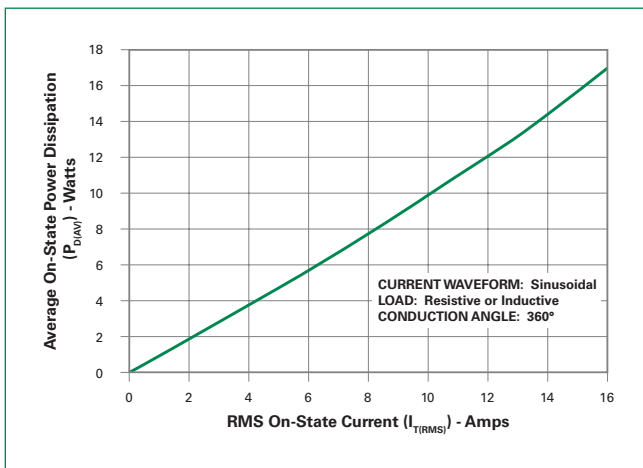
**Figure 3: Normalized DC Holding Current vs. Junction Temperature**



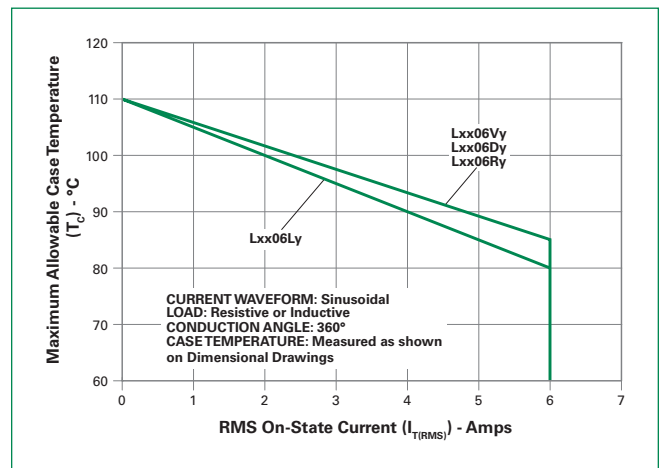
**Figure 4: Normalized DC Gate Trigger Voltage for All Quadrants vs. Junction Temperature**



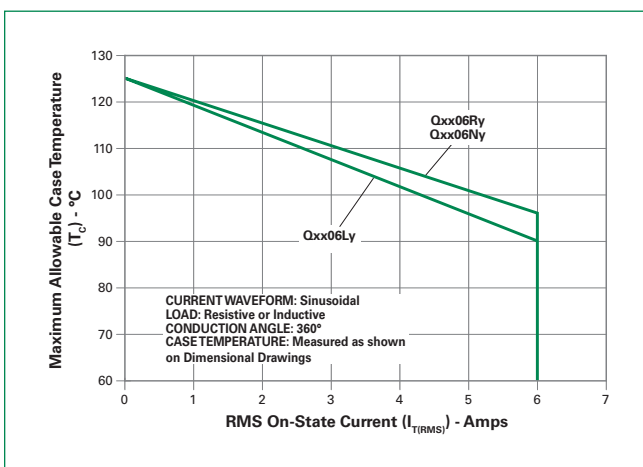
**Figure 5: Power Dissipation (Typical) vs. RMS On-State Current**



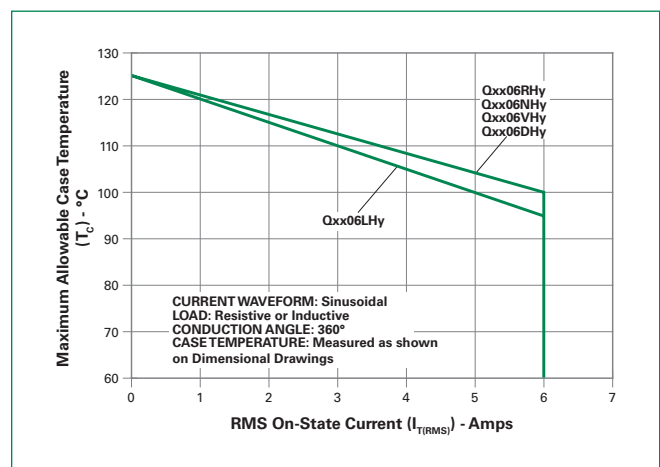
**Figure 6: Maximum Allowable Case Temperature vs. On-State Current (Sensitive Triac)**



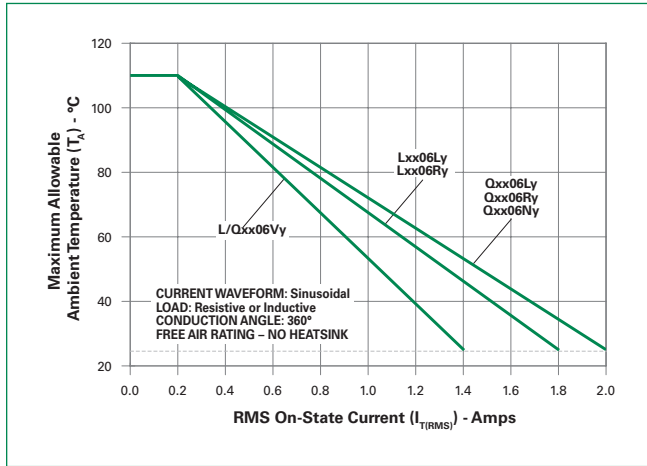
**Figure 7: Maximum Allowable Case Temperature vs. On-State Current (Standard Triac)**



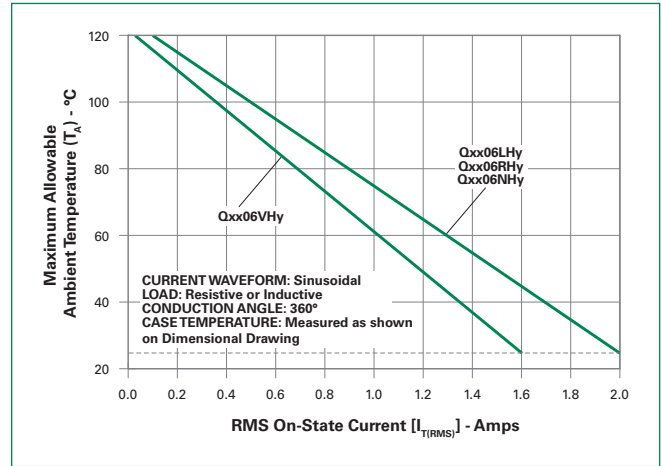
**Figure 8: Maximum Allowable Case Temperature vs. On-State Current (Alternistor Triac)**



**Figure 9: Maximum Allowable Ambient Temperature vs. On-State Current (Sensitive / Standard Triac)**



**Figure 10: Maximum Allowable Ambient Temperature vs. On-State Current (Alternistor Triac)**



**Figure 11: On-State Current vs. On-State Voltage (Typical)**

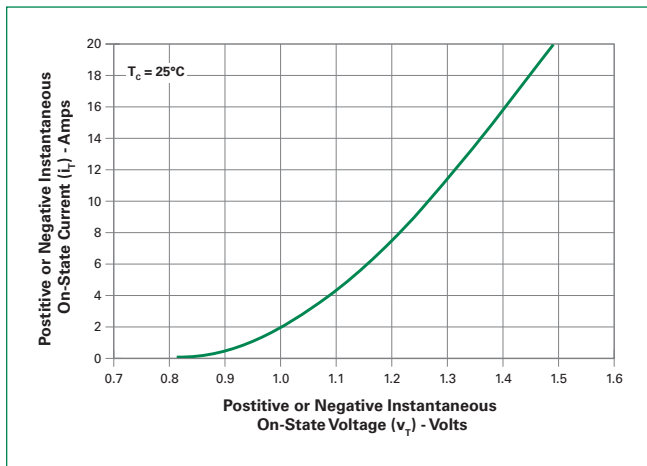


Figure 12: Surge Peak On-State Current vs. Number of Cycles (Sensitive / Standard Triac)

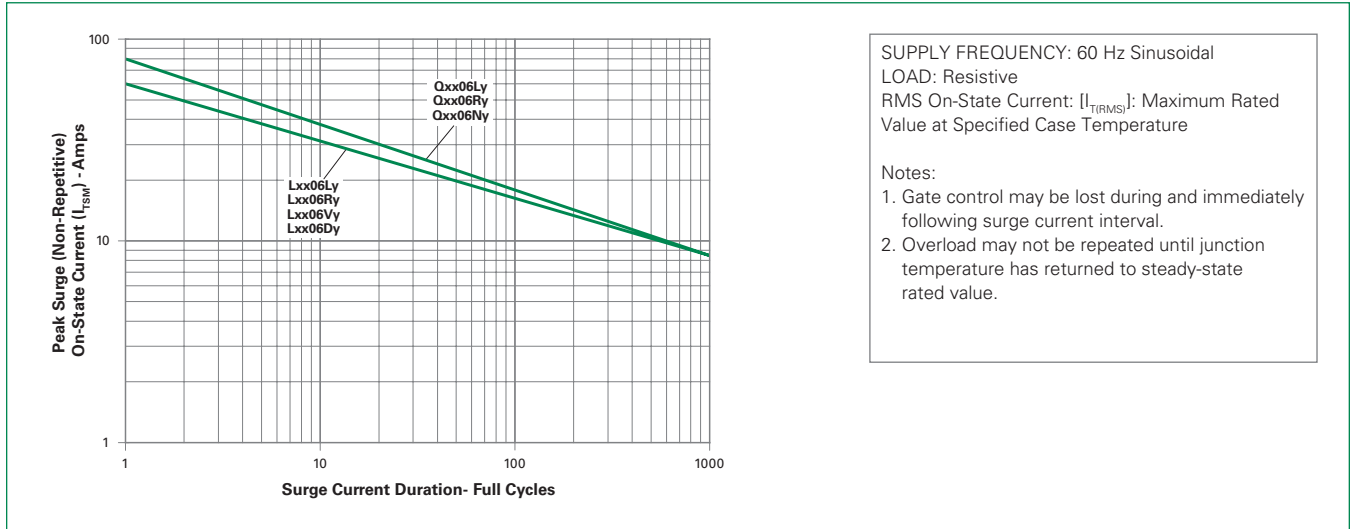
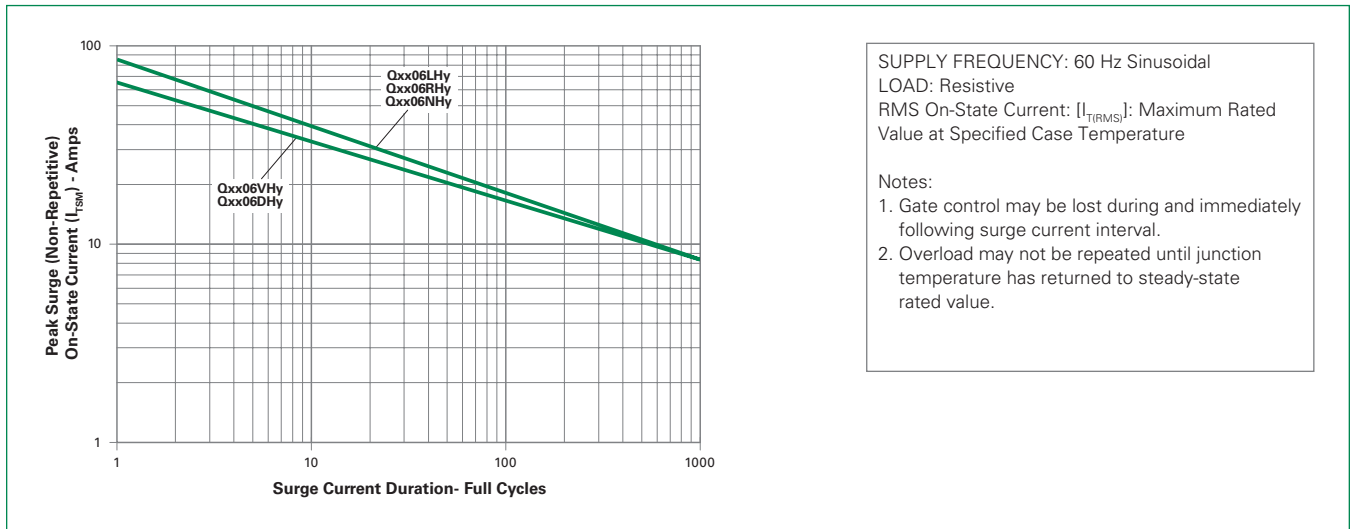


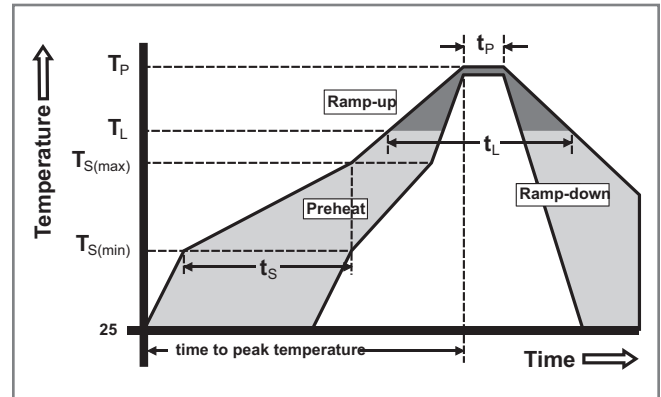
Figure 13: Surge Peak On-State Current vs. Number of Cycles (Alternistor Triac)



Note: xx = voltage, x = package, y = sensitivity, yy = type & sensitivity

**Soldering Parameters**

Reflow Condition		Pb – Free assembly
Pre Heat	- Temperature Min ( $T_{s(min)}$ )	150°C
	- Temperature Max ( $T_{s(max)}$ )	200°C
	- Time (min to max) ( $t_s$ )	60 – 180 secs
Average ramp up rate (Liquidus Temp ( $T_L$ ) to peak)		5°C/second max
$T_{s(max)}$ to $T_L$ - Ramp-up Rate		5°C/second max
Reflow	- Temperature ( $T_L$ ) (Liquidus)	217°C
	- Temperature ( $t_L$ )	60 – 150 seconds
Peak Temperature ( $T_p$ )		260 <sup>+0/-5</sup> °C
Time within 5°C of actual peak Temperature ( $t_p$ )		20 – 40 seconds
Ramp-down Rate		5°C/second max
Time 25°C to peak Temperature ( $T_p$ )		8 minutes Max.
Do not exceed		280°C



**Physical Specifications**

<b>Terminal Finish</b>	100% Matte Tin-plated
<b>Body Material</b>	UL recognized epoxy meeting flammability classification 94V-0
<b>Terminal Material</b>	Copper Alloy

**Design Considerations**

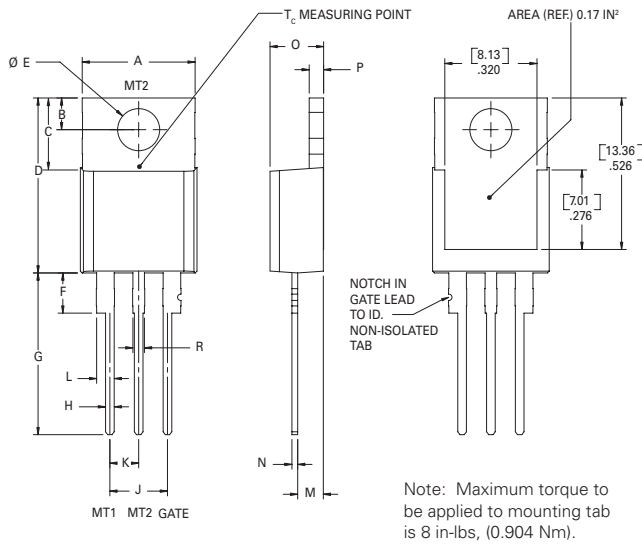
Careful selection of the correct device for the application's operating parameters and environment will go a long way toward extending the operating life of the Thyristor. Good design practice should limit the maximum continuous current through the main terminals to 75% of the device rating. Other ways to ensure long life for a power discrete semiconductor are proper heat sinking and selection of voltage ratings for worst case conditions. Overheating, overvoltage (including dv/dt), and surge currents are the main killers of semiconductors. Correct mounting, soldering, and forming of the leads also help protect against component damage.

**Environmental Specifications**

Test	Specifications and Conditions
<b>AC Blocking (<math>V_{DRM}</math>)</b>	MIL-STD-750, M-1040, Cond A Applied Peak AC voltage @ 125°C for 1008 hours
<b>Temperature Cycling</b>	MIL-STD-750, M-1051, 100 cycles; -40°C to +150°C; 15-min dwell-time
<b>Temperature/Humidity</b>	EIA / JEDEC, JESD22-A101 1008 hours; 320V - DC: 85°C; 85% rel humidity
<b>High Temp Storage</b>	MIL-STD-750, M-1031, 1008 hours; 150°C
<b>Low-Temp Storage</b>	1008 hours; -40°C
<b>Thermal Shock</b>	MIL-STD-750, M-1056 10 cycles; 0°C to 100°C; 5-min dwell-time at each temperature; 10 sec (max) transfer time between temperature
<b>Autoclave</b>	EIA / JEDEC, JESD22-A102 168 hours (121°C at 2 ATMs) and 100% R/H
<b>Resistance to Solder Heat</b>	MIL-STD-750 Method 2031
<b>Solderability</b>	ANSI/J-STD-002, category 3, Test A
<b>Lead Bend</b>	MIL-STD-750, M-2036 Cond E

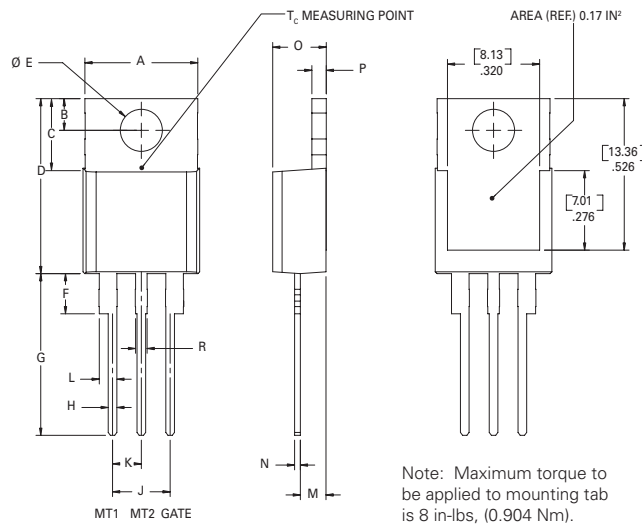


## Dimensions — TO-220AB (R-Package) — Non-Isolated Mounting Tab Common with Center Lead



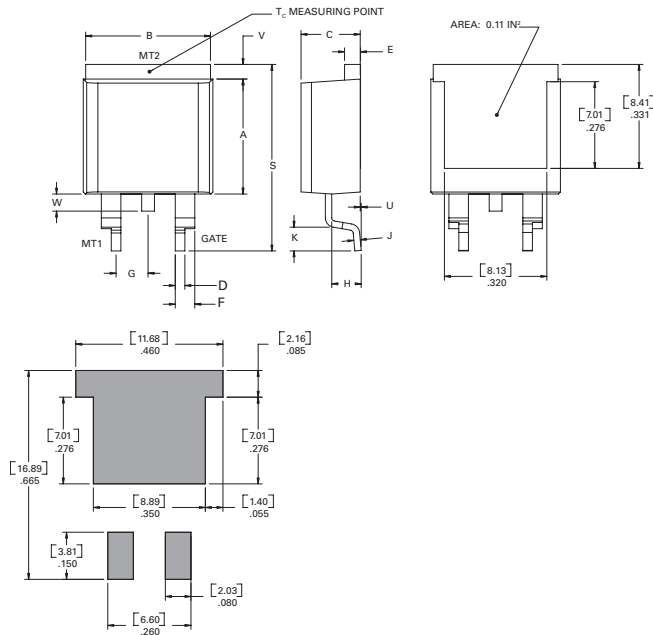
Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.380	0.420	9.65	10.67
B	0.105	0.115	2.67	2.92
C	0.230	0.250	5.84	6.35
D	0.590	0.620	14.99	15.75
E	0.142	0.147	3.61	3.73
F	0.110	0.130	2.79	3.30
G	0.540	0.575	13.72	14.61
H	0.025	0.035	0.64	0.89
J	0.195	0.205	4.95	5.21
K	0.095	0.105	2.41	2.67
L	0.060	0.075	1.52	1.91
M	0.085	0.095	2.16	2.41
N	0.018	0.024	0.46	0.61
O	0.178	0.188	4.52	4.78
P	0.045	0.060	1.14	1.52
R	0.038	0.048	0.97	1.22

## Dimensions — TO-220AB (L-Package) — Isolated Mounting Tab



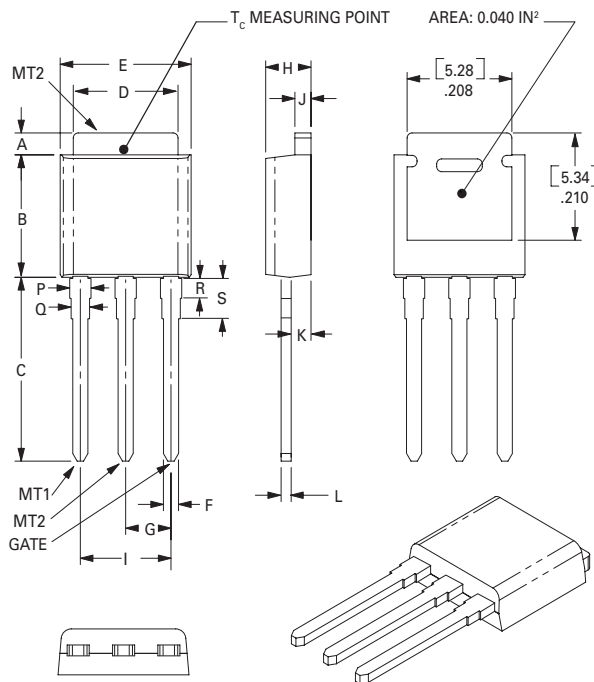
Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.380	0.420	9.65	10.67
B	0.105	0.115	2.67	2.92
C	0.230	0.250	5.84	6.35
D	0.590	0.620	14.99	15.75
E	0.142	0.147	3.61	3.73
F	0.110	0.130	2.79	3.30
G	0.540	0.575	13.72	14.61
H	0.025	0.035	0.64	0.89
J	0.195	0.205	4.95	5.21
K	0.095	0.105	2.41	2.67
L	0.060	0.075	1.52	1.91
M	0.085	0.095	2.16	2.41
N	0.018	0.024	0.46	0.61
O	0.178	0.188	4.52	4.78
P	0.045	0.060	1.14	1.52
R	0.038	0.048	0.97	1.22

## Dimensions — TO-263AB (N-Package) — D<sup>2</sup>-PAK Surface Mount



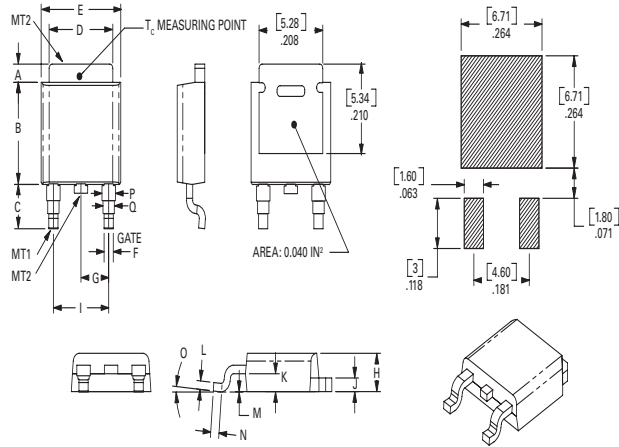
Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.360	0.370	9.14	9.40
B	0.380	0.420	9.65	10.67
C	0.178	0.188	4.52	4.78
D	0.025	0.035	0.64	0.89
E	0.045	0.060	1.14	1.52
F	0.060	0.075	1.52	1.91
G	0.095	0.105	2.41	2.67
H	0.092	0.102	2.34	2.59
J	0.018	0.024	0.46	0.61
K	0.090	0.110	2.29	2.79
S	0.590	0.625	14.99	15.88
V	0.035	0.045	0.89	1.14
U	0.002	0.010	0.05	0.25
W	0.040	0.070	1.02	1.78

## Dimensions — TO-251AA (V-Package) — V-PAK Through Hole



Dimension	Inches			Millimeters		
	Min	Typ	Max	Min	Typ	Max
A	0.040	0.044	0.050	1.02	1.11	1.27
B	0.235	0.242	0.245	5.97	6.15	6.22
C	0.350	0.361	0.375	8.89	9.18	9.53
D	0.205	0.208	0.213	5.21	5.29	5.41
E	0.255	0.262	0.265	6.48	6.66	6.73
F	0.027	0.031	0.033	0.69	0.80	0.84
G	0.087	0.090	0.093	2.21	2.28	2.36
H	0.085	0.092	0.095	2.16	2.34	2.41
I	0.176	0.180	0.184	4.47	4.57	4.67
J	0.018	0.020	0.023	0.46	0.51	0.58
K	0.038	0.040	0.044	0.97	1.01	1.12
L	0.018	0.020	0.023	0.46	0.52	0.58
P	0.042	0.047	0.052	1.06	1.20	1.32
Q	0.034	0.039	0.044	0.86	1.00	1.11
R	0.034	0.039	0.044	0.86	1.00	1.11
S	0.074	0.079	0.084	1.86	2.00	2.11

**Dimensions — TO-252AA (D-Package) — D-PAK Surface mount**



Dimension	Inches			Millimeters		
	Min	Typ	Max	Min	Typ	Max
A	0.040	0.043	0.050	1.02	1.09	1.27
B	0.235	0.243	0.245	5.97	6.16	6.22
C	0.106	0.108	0.113	2.69	2.74	2.87
D	0.205	0.208	0.213	5.21	5.29	5.41
E	0.255	0.262	0.265	6.48	6.65	6.73
F	0.027	0.031	0.033	0.69	0.80	0.84
G	0.087	0.090	0.093	2.21	2.28	2.36
H	0.085	0.092	0.095	2.16	2.33	2.41
I	0.176	0.179	0.184	4.47	4.55	4.67
J	0.018	0.020	0.023	0.46	0.51	0.58
K	0.038	0.040	0.044	0.97	1.02	1.12
L	0.018	0.020	0.023	0.46	0.51	0.58
M	0.000	0.000	0.004	0.00	0.00	0.10
N	0.021	0.026	0.027	0.53	0.67	0.69
O	0°	0°	5°	0°	0°	5°
P	0.042	0.047	0.052	1.06	1.20	1.32
Q	0.034	0.039	0.044	0.86	1.00	1.11

**Product Selector**

Part Number	Voltage				Gate Sensitivity Quadrants		Type	Package
	400V	600V	800V	1000V	I - II - III	IV		
Lxx06L5	X	X			5 mA	5 mA	Sensitive Triac	TO-220L
Lxx06D5	X	X			5 mA	5 mA	Sensitive Triac	TO-252 D-PAK
Lxx06R5	X	X			5mA	5mA	Sensitive Triac	TO-220R
Lxx06V5	X	X			5 mA	5 mA	Sensitive Triac	TO-251 V-PAK
Lxx06L6	X	X			5 mA	10 mA	Sensitive Triac	TO-220L
Lxx06D6	X	X			5 mA	10 mA	Sensitive Triac	TO-252 D-PAK
Lxx06R6	X	X			5mA	10mA	Sensitive Triac	TO-220R
Lxx06V6	X	X			5 mA	10 mA	Sensitive Triac	TO-251 V-PAK
Lxx06L8	X	X			10 mA	20 mA	Sensitive Triac	TO-220L
Lxx06D8	X	X			10 mA	20 mA	Sensitive Triac	TO-252 D-PAK
Lxx06R8	X	X			10mA	20mA	Sensitive Triac	TO-220R
Lxx06V8	X	X			10 mA	20 mA	Sensitive Triac	TO-251 V-PAK
Qxx06VH3	X	X			10 mA		Alternistor Triac	TO-251 V-PAK
Qxx06DH3	X	X			10 mA		Alternistor Triac	TO-252 D-PAK
Qxx06L4	X				25 mA		Standard Triac	TO-220L
Qxx06R4	X				25 mA		Standard Triac	TO-220R
Qxx06N4	X				25 mA		Standard Triac	TO-263 D <sup>2</sup> -PAK
Qxx06RH3	X	X			10mA		Alternistor Triac	TO-220R
Qxx06LH4	X	X	X	X	35 mA		Alternistor Triac	TO-220L
Qxx06RH4	X	X	X	X	35 mA		Alternistor Triac	TO-220R
Qxx06VH4	X	X	X	X	35 mA		Alternistor Triac	TO-251 V-PAK
Qxx06DH4	X	X	X	X	35 mA		Alternistor Triac	TO-252 D-PAK
Qxx06NH4	X	X	X	X	35 mA		Alternistor Triac	TO-263 D <sup>2</sup> -PAK
Qxx06L5		X	X	X	50 mA		Standard Triac	TO-220L
Qxx06R5		X	X	X	50 mA		Standard Triac	TO-220R
Qxx06N5		X	X	X	50 mA		Standard Triac	TO-263 D <sup>2</sup> -PAK

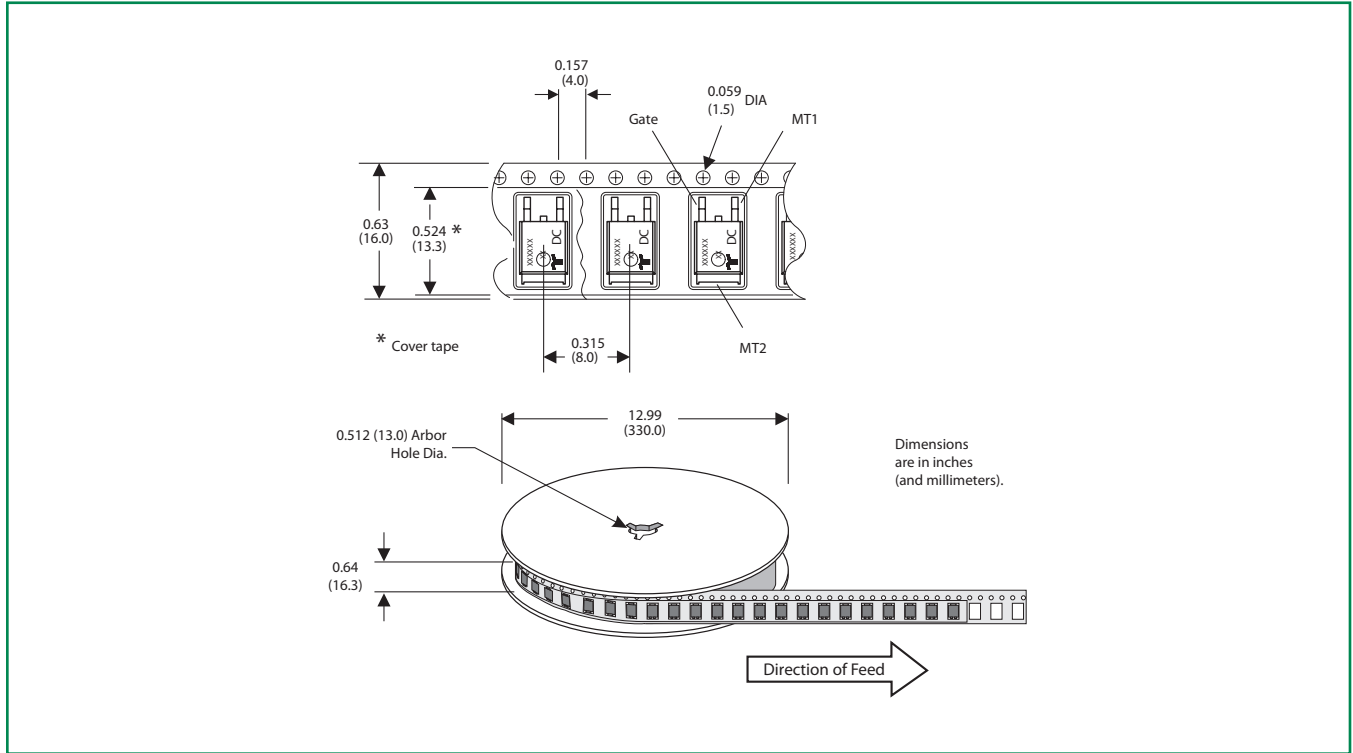
**Packing Options**

Part Number	Marking	Weight	Packing Mode	Base Quantity
Lxx06L/Ry	Lxx06L/Ry	2.2 g	Bulk	500
Lxx06L/RyTP	Lxx06L/Ry	2.2 g	Tube Pack	500 (50 per tube)
Lxx06DyTP	Lxx06Dy	0.3 g	Tube	750 (75 per tube)
Lxx06DyRP	Lxx06Dy	0.3 g	Embossed Carrier	2500
Lxx06VyTP	Lxx06Vy	0.4 g	Tube	750 (75 per tube)
Qxx06L/Ryy	Qxx06L/Ryy	2.2 g	Bulk	500
Qxx06L/RyyTP	Qxx06L/Ryy	2.2 g	Tube Pack	500 (50 per tube)
Qxx06NyyTP	Qxx06Nyy	1.6 g	Tube	500 (50 per tube)
Qxx06NyyRP	Qxx06Nyy	1.6 g	Embossed Carrier	500
Qxx06DyyTP	Qxx06Dyy	0.3 g	Tube	750 (75 per tube)
Qxx06DyyRP	Qxx06Dyy	0.3 g	Embossed Carrier	2500
Qxx06VyyTP	Qxx06Vyy	0.4 g	Tube	750 (75 per tube)

Note: xx = voltage; yy = sensitivity

**TO-252 Embossed Carrier Reel Pack (RP) Specifications**

Meets all EIA-481-2 Standards

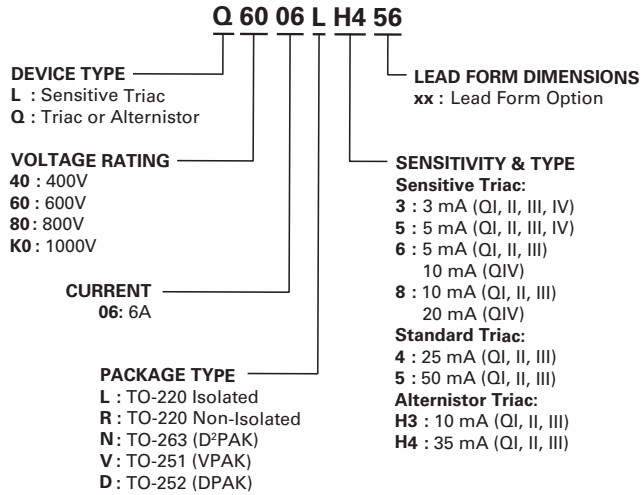


**TO-263 Embossed Carrier Reel Pack (RP) Specifications**

Meets all EIA-481-2 Standards



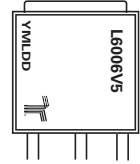
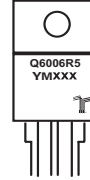
### Part Numbering System



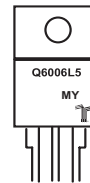
### Part Marking System

TO-220 AB – (R Package)  
 TO-263 AB – (N Package)

TO-252AA – (D Package)  
 TO-251AA – (V Package)



TO-220 AB – (L Package)





## Стандарт Электрон Связь

Мы молодая и активно развивающаяся компания в области поставок электронных компонентов. Мы поставляем электронные компоненты отечественного и импортного производства напрямую от производителей и с крупнейших складов мира.

Благодаря сотрудничеству с мировыми поставщиками мы осуществляем комплексные и плановые поставки широчайшего спектра электронных компонентов.

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С нами вы становитесь еще успешнее!

### Наши контакты:

**Телефон:** +7 812 627 14 35

**Электронная почта:** [sales@st-electron.ru](mailto:sales@st-electron.ru)

**Адрес:** 198099, Санкт-Петербург,  
Промышленная ул, дом № 19, литера Н,  
помещение 100-Н Офис 331